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Fairchild Semiconductor MMBT2222

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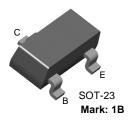
Datasheet of MMBT2222 - TRANS NPN 30V 0.6A SOT-23 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



MMBT2222

NPN General Purpose Amplifier

• Sourced from process 19.



Absolute Maximum Ratings* T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	0.6	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

^{*} This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		10	μΑ
		$V_{CB} = 50V, I_{E} = 0, T_{a} = 125^{\circ}C$		10	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{V}, I_{C} = 0$		10	nA
On Charac	cteristics				
h _{FE}	DC Current Gain	$I_C = 0.1 \text{mA}, V_{CE} = 10 \text{V}$	35		
		$I_C = 1.0 \text{mA}, V_{CE} = 10 \text{V}$	50		
		$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}$	75		
		$I_C = 150 \text{mA}, V_{CE} = 10 \text{V}^*$	100	300	
		$I_C = 150 \text{mA}, V_{CF} = 1.0 \text{V}^*$	50		
		I _C = 500mA, V _{CE} = 10V *	30		
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 150mA, I _B = 15V		0.4	V
V/		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		1.6	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150mA, I _B = 15V		1.3	V
. ,		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		2.6	

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Electrical Characteristics (Continued) T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Small Signal Characteristics						
f _T	Curent Gain Bandwidth Product	I _C = 20mA, V _{CE} = 20V, f = 100MHz	250			
C _{obo}	Output Capacitance	V _{CB} = 10V, I _E = 0, f = 1MHz		8.0	pF	
C _{ibo}	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$		30	pF	
Switching Characteristics						
t _d	Delay Time	$V_{CC} = 30V, V_{BE(OFF)} = 0.5V,$		10	ns	
t _r	Rise Time	I _C = 150mA, I _{B1} = 15mA		25	ns	
t _s	Storage Time	V _{CC} = 30V, I _C = 150mA,		225	ns	
t _f	Fall Time	$I_{B1} = I_{B2} = 15\text{mA}$		60	ns	

^{*} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%

Thermal Characteristics T_a=25°C unless otherwise noted

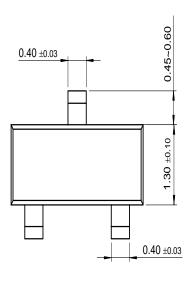
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

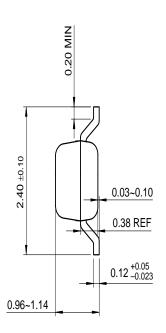
^{*} Device mounted on FR-4PCB 1.6" × 1.6" × 0.06".

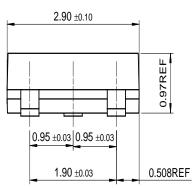
MMBT2222

Package Dimensions

SOT-23







Dimensions in Millimeters

Distributor of Fairchild Semiconductor: Excellent Integrated System Limited

Datasheet of MMBT2222 - TRANS NPN 30V 0.6A SOT-23

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Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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